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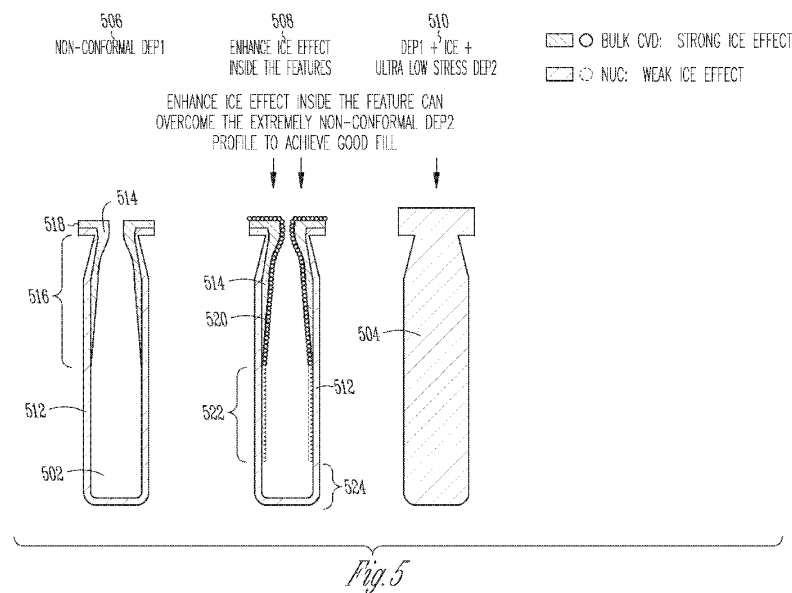
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(54) Title: TUNGSTEN FEATURE FILL WITH INHIBITION CONTROL



(57) Abstract: Systems and methods for selective inhibition control in semiconductor manufacturing are provided. An example method includes providing a substrate including a feature having one or more feature openings and a feature interior. A nucleation layer is formed on a surface of the feature interior. Based on a differential inhibition profile, a nonconformal bulk layer is selectively formed on a surface of the nucleation layer to leave a region of the nucleation layer covered, and a region of the nucleation layer uncovered by the nonconformal bulk layer. An inhibition layer is selectively formed on the covered and uncovered regions of the nucleation layer. Tungsten is deposited in the feature in accordance with the differential inhibition profile.

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